

SAI RAJESWARI INSTITUTE OF TECHNOLOGY

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Application form to claim the Incentive

Name and Designation of the					
faculty					
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Contact details	Mobile:			E-mail:	
Title of the					
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Journal or Patent details	ISSN No/ Patent Application number	Interna tional / Nation al	Publication month & year	Issue no, volume no, page no.	Impact factor of Journal
Conference/					
Workshops/	Venue and	International		Publication	Page no. of
FDPs details	duration	/National Conference		month & year of proceeding	proceedings

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Documents attached (Xerox):

- 1. Sanction order and proof of receipt of grants to the Institute
- 2. Hard copy of the complete paper/patent (Final Print after publishing)
- 3. Copy of Registration Fee/Processing Fee Receipt
- 4. Participation & Presentation certificate
- 5. Other any proof.

Date:

Recommendations of the

HOD

A copy of the published paper submitted in the department?

(Yes/No)

Amount recommended after scrutiny of details submitted:

Date:

Signature of the HOD

Signature of the Faculty

Verified by Dean, R&D

Date:

Amount approved/not approved by the Principal:

Date:

Signature of the Principal

Signature of the Dean R&D